

## Claims

[c1] What is claimed is:

1. A method for manufacturing a multi-slants reflector, comprising the steps of:  
providing a substrate;  
forming a plurality of thin film transistors and a plurality of multi-layered structures on the substrate simultaneously; and  
coating an organic layer on said thin film transistors and said multi-layered structures;  
performing a baking step to smooth the organic layer so as to form a plurality of asymmetric slants; and  
forming a reflective metal layer on the organic layer.

[c2] 2. The method of claim 1 for manufacturing a multi-slants reflector, wherein each of said asymmetric slants has substantially different angles between an upper surface of the reflective metal layer and an upper surface of the substrate.

[c3] 3. The method of claim 1 for manufacturing a multi-slants reflector, wherein each of said asymmetric slants has substantially different heights.

[c4] 4. The method of claim 1 for manufacturing a multi-slants reflector, wherein each of said asymmetric slants comprises a multi-layered structure, and each layer of said multi-layered structure has substantially different widths.

[c5] 5. The method of claim 4 for manufacturing a multi-slants reflector, wherein said multi-layered structure is a random composition of a gate metal layer, an insulation layer, an a-Si layer, an  $N^+$  layer, and a source/drain metal layer.

[c6] 6. The method of claim 2 for manufacturing a multi-slants reflector, wherein said angles ranging from 0 degrees to about approximately 10 degrees.

[c7] 7. A multi-slants reflector applied in a liquid crystal display (LCD), and the multi-slants reflector comprising:  
a substrate;  
a plurality of thin film transistors disposed on the substrate;  
a reflective metal layer;

a plurality of asymmetric slants, each comprising a multi-layered structure, located between the substrate and the reflective metal layer; and an organic layer located between said reflective metal layer and said multi-layered structure.

[c8] 8. A multi-slants reflector according to claim 7, wherein each of said asymmetric slants has substantially different angles between an upper surface of the reflective metal layer and an upper surface of the substrate.

[c9] 9. A multi-slants reflector according to claim 7, wherein each of said asymmetric slants has substantially different heights.

[c10] 10. A multi-slants reflector according to claim 7, wherein each layer of said multi-layered structure has substantially different widths.

[c11] 11. A multi-slants reflector according to claim 7, wherein said multi-layered structure is a random composition of a gate metal layer, an insulation layer, an a-Si layer, an N<sup>+</sup> layer, and a source/drain metal layer.

[c12] 12. A multi-slants reflector according to claim 8, wherein said angles range from 0 degrees to about approximately 10 degrees.

[c13] 13. A method for manufacturing a multi-slants reflector, comprising the steps of:

providing a substrate;

forming a plurality of thin film transistors and a plurality of multi-layered structures on the substrate simultaneously;

coating a protection layer on said thin film transistors and said multi-layered structures; and

forming a reflective metal layer on said protection layer.